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**Graphene synthesis, carbon foams, pillared
graphene, pseudospheres and all that from
first-principles, multiscale simulations and
experiments**

20 September 2017 - RPPGR2017, Singapore

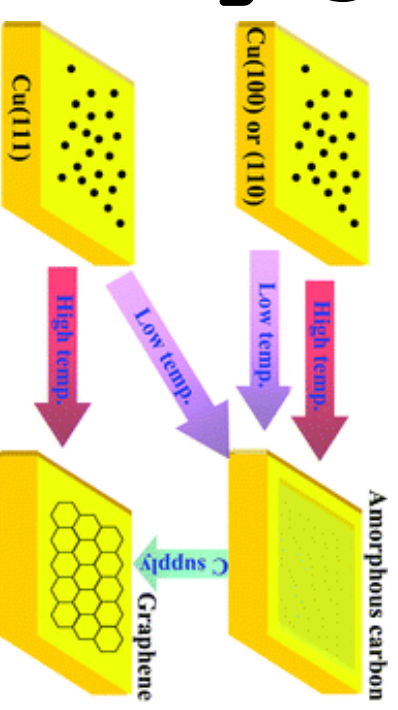
Motivation and outline of the work

Can we think a more exotic way, cheaper and lower in temperature, to produce SiC and graphene? **Supersonic Molecular Beam Epitaxy (SuMBE): how to grow materials at low T in a way conceptually different from what used so far.**

Due to the rarity in nature, SiC and graphene are typically synthesised using heteroepitaxy on Si or CVD on metals.

These procedures are plagued by three similar drawbacks:

- high processing temperature ($T > 1200\text{ K}$)
- high lattice/thermal exp. coeff. mismatch
- Si diffusion through the SiC film or C segregation



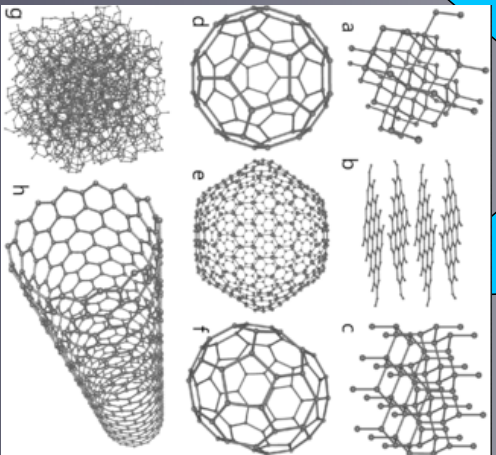
Temperature can cause defects and high cost, no scalability

Can computational modelling help our understanding (and thus controlling and designing) the growth mechanisms of materials?

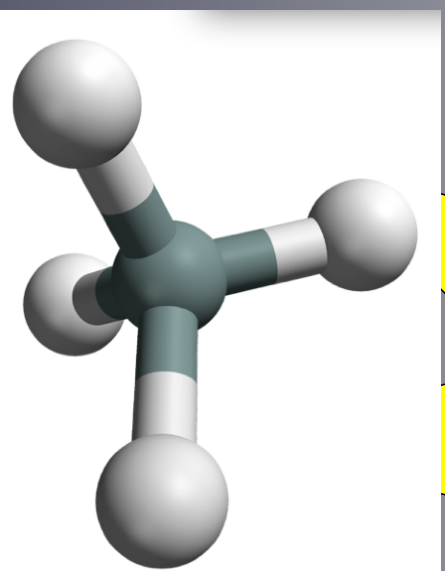
First example: SiC growth at room T

No doubt you need silicon and carbon to build SiC

Carbon exists in many shapes



+



=

?

Silicon comes as inorganic compounds
silane family
or
bulk

Our building blocks: Si(111) and C₆₀



GOOD FOR SUMBE:

No hydrogen or oxygen

Mechanically and chemically stable but not totally unreactive (electronegative) as the carbon atoms are sp²-hybridized

Cheap, sublimates below T=800 K

Simple to accelerate and massive

ELECTRONIC PROPERTIES of C₆₀:

Semicond: 1.6 eV in the ground state

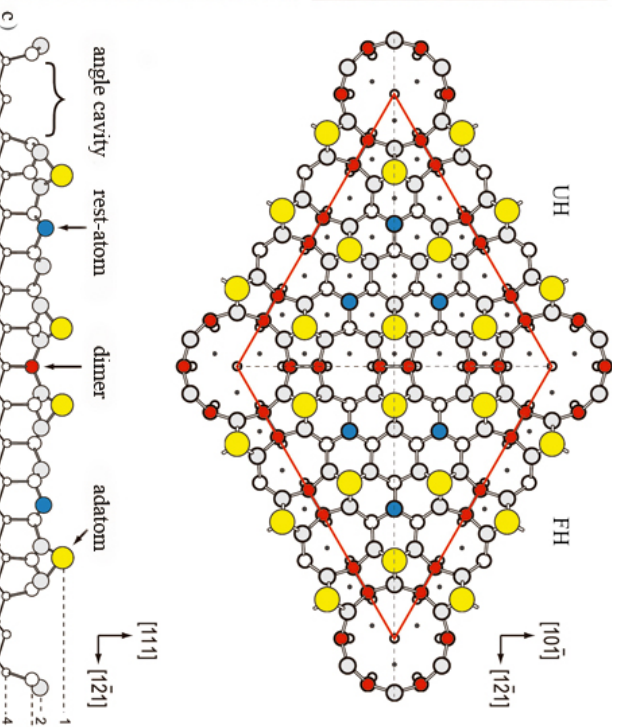
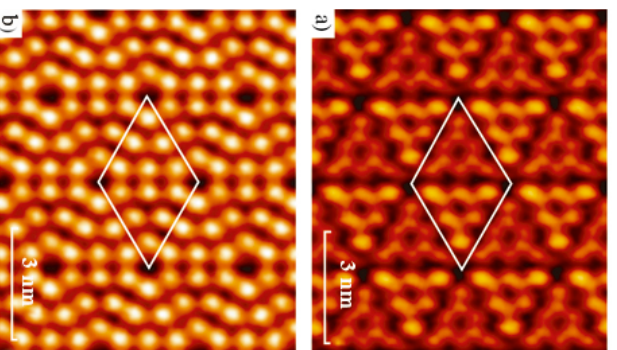
Aromatic but not superaromatic (K)

Si(111) reconstructed surface:
cleave along 111 direction

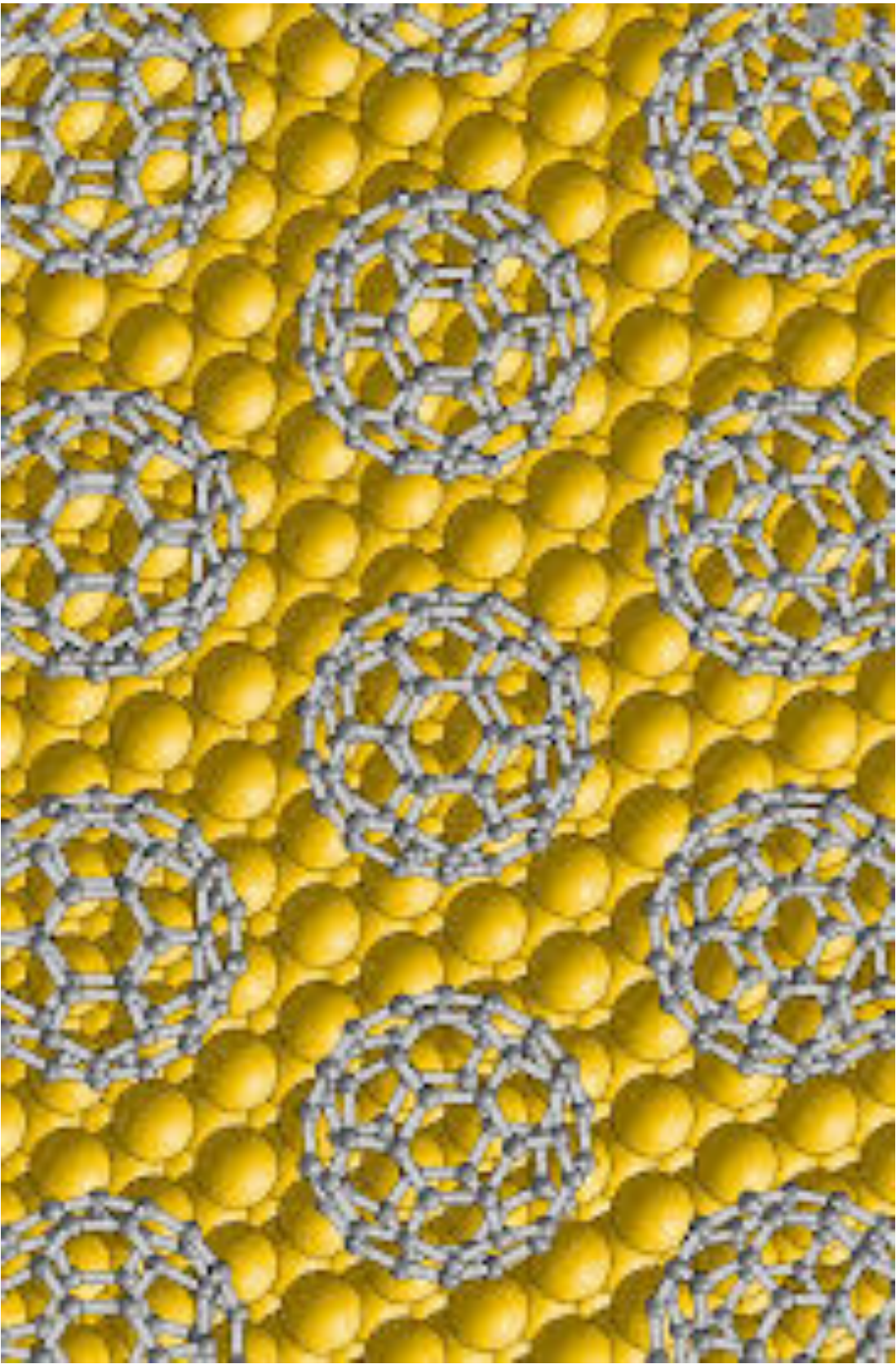
GOOD FOR SUMBE:

19 dangling bonds make this surface very reactive

STM image A success story of DFT



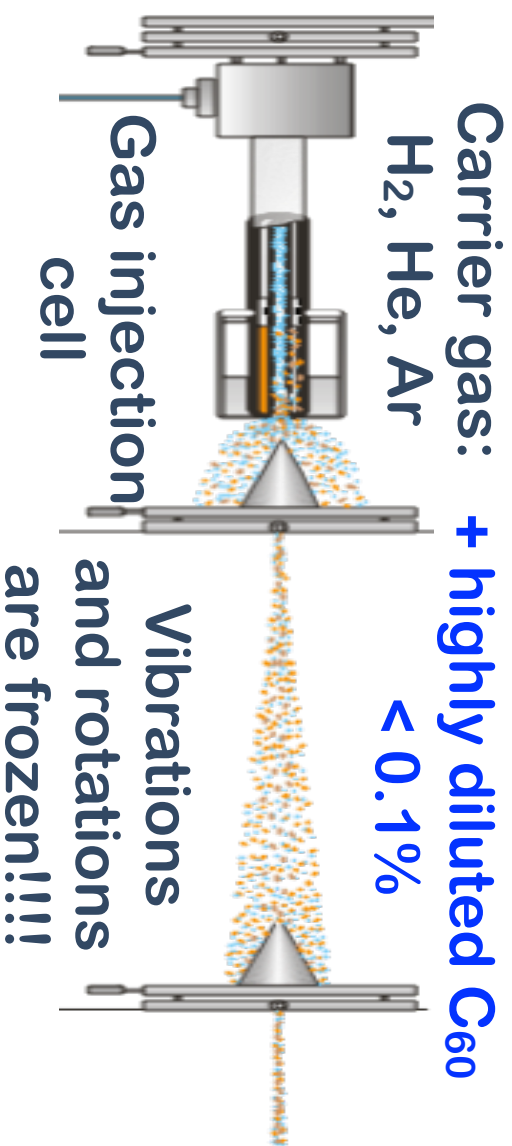
Luca Pacioli
"De Divina
proportione"
1509



NO WAY!!!

The SUMBE approach

Highly diluted supersonic beams are appealing for both organic thin films and cluster-assembled nanomaterials depositions.



- A first experiment of deposition (carrier gas: **He**) gave evidence of SiC islands formation at 800 K for a C₆₀ kinetic energy of 20 eV (not below though).

- A second experiment (carrier gas: **H₂**) at higher C₆₀ kinetic energy (30 to 35 eV) formed SiC islands at room T.

Continuous supersonic molecular beam source

In a quartz tube an inert carrier gas is seeded with species sublimated by Joule heating. The mixture then expands into vacuum through a nozzle. Kinetic energy can be tuned by changing the carrier gas and the seeding parameters (source temperature, gas inlet pressure).

TRANSLATIONAL KINETIC ENERGY

Aerodynamic acceleration

up to tens of eV!!

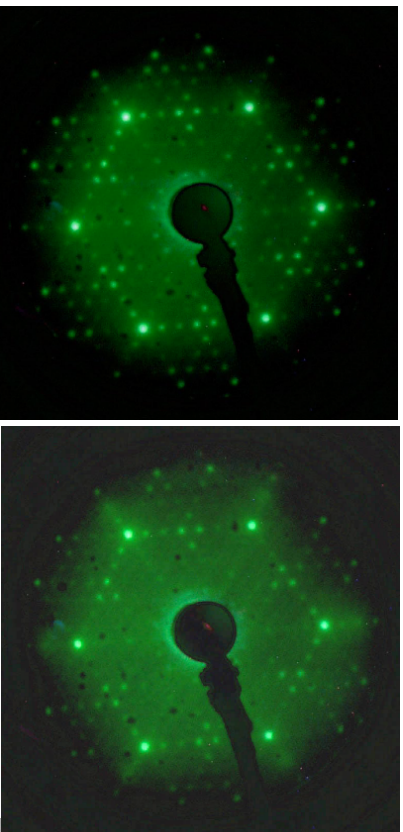
For MBE, KE~0.05eV

$$E_K^i \approx (m_i / \langle m \rangle) T_0$$

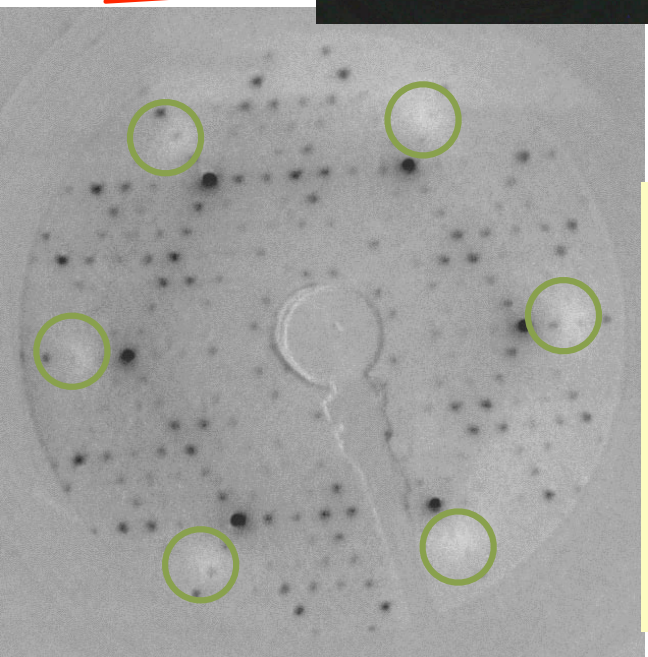
$$\langle m \rangle = \sum_i X_i m_i$$

$C_{60}/Si(111)7\times 7$ @ RT: structural properties

0.70 ML $C_{60}/Si(111)7 \times 7$
film formed @ 35 eV KE

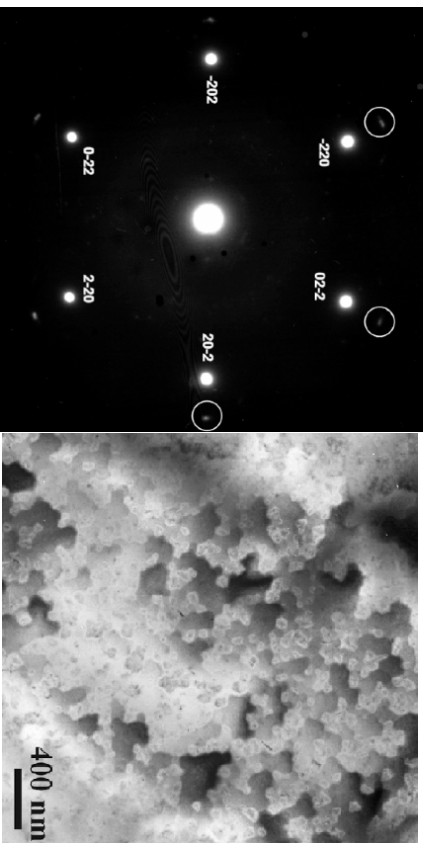


LEED analysis

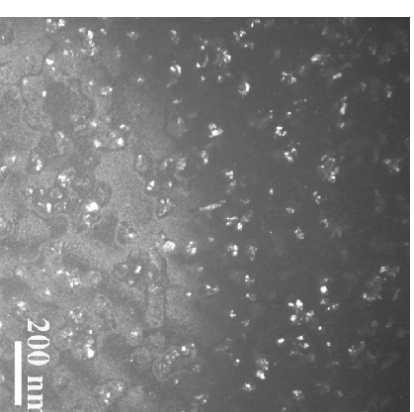
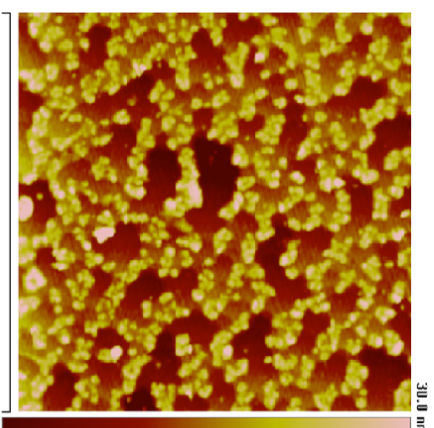


-20% lattice parameter vs. Si, typical of **3C-SiC!**
Nanoislands >20nm

TEM analysis

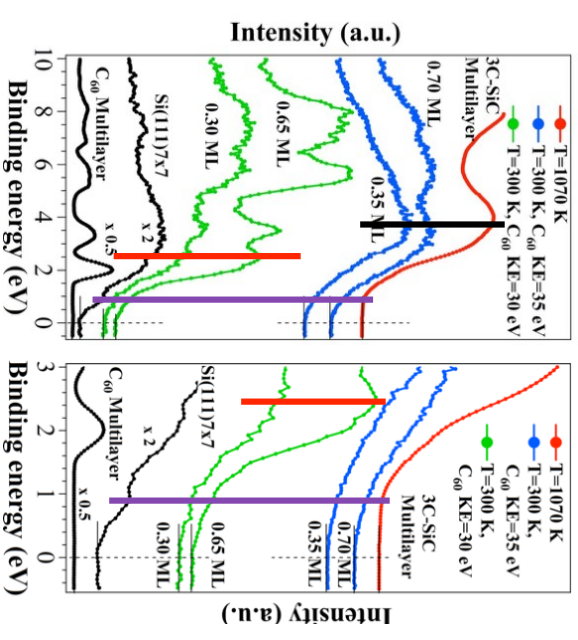


AFM analysis



Si(111) bright spots
and weak reflections
from the 3C-SiC
phase (circled spots)

3C-SiC nanocrystalline
islands, <10nm, with a
completely relaxed lattice!



CAKE WITHOUT COOKING IN 3 MOVES



Kinetically driven synthesis of SiC (obtained by supersonic beams implanted with C_{60}) is a promising technique able to reduce drastically the growth temperature and increase structural order...for the first time SiC ordered domains have been observed at such a low temperature.

Open questions for theory

What is the nature of the chemical-physical processes at the film/Si interface?

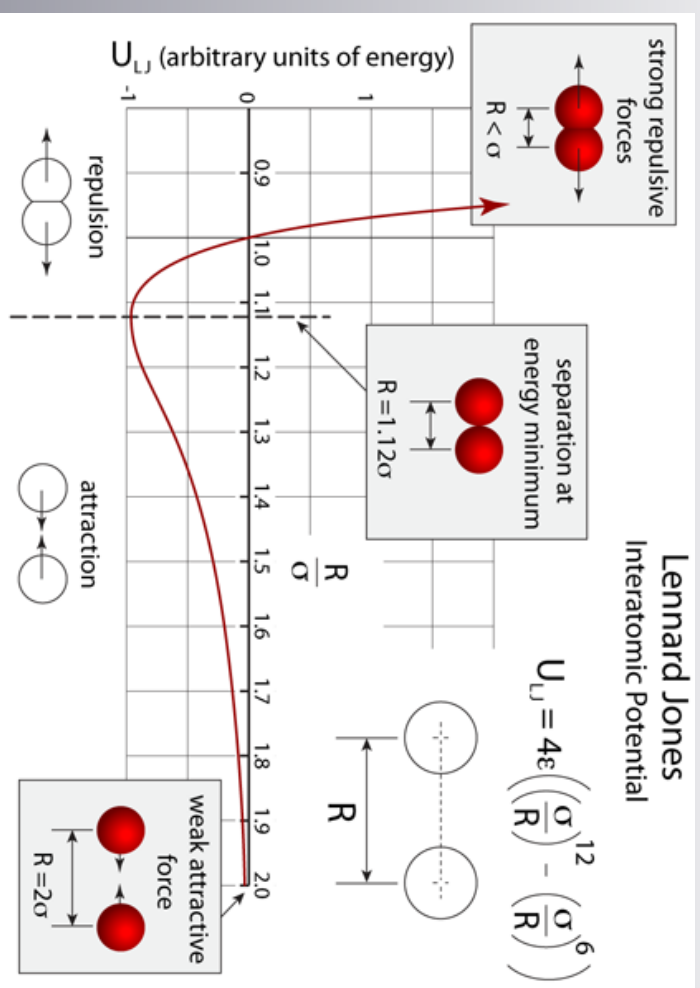
Can we model the SiC synthesis by using classical, quantum mechanics and multiscale approaches?

What is the C_{60} beam KE threshold for the Si-C covalent bond formation?



First approach: Molecular Mechanics

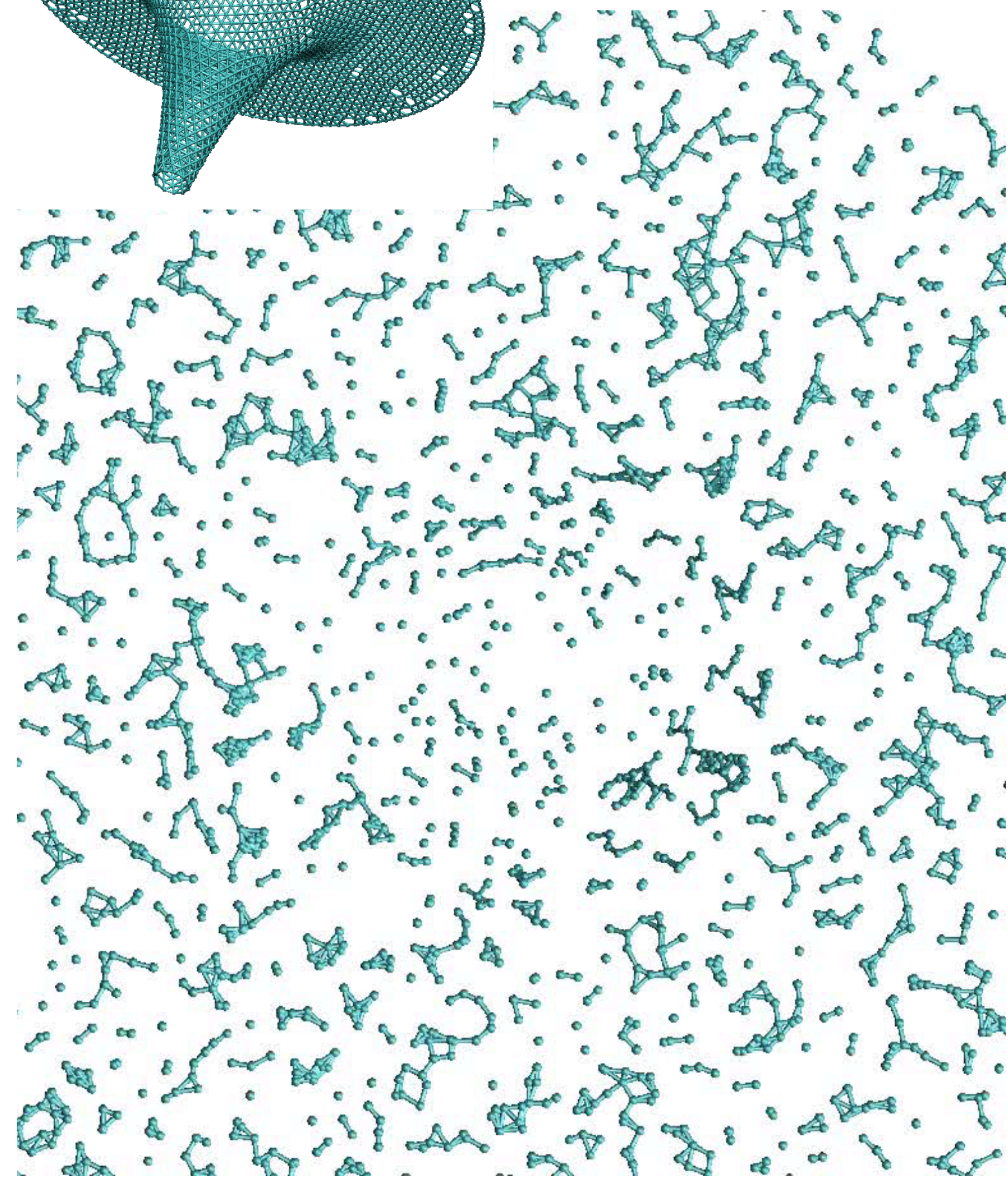
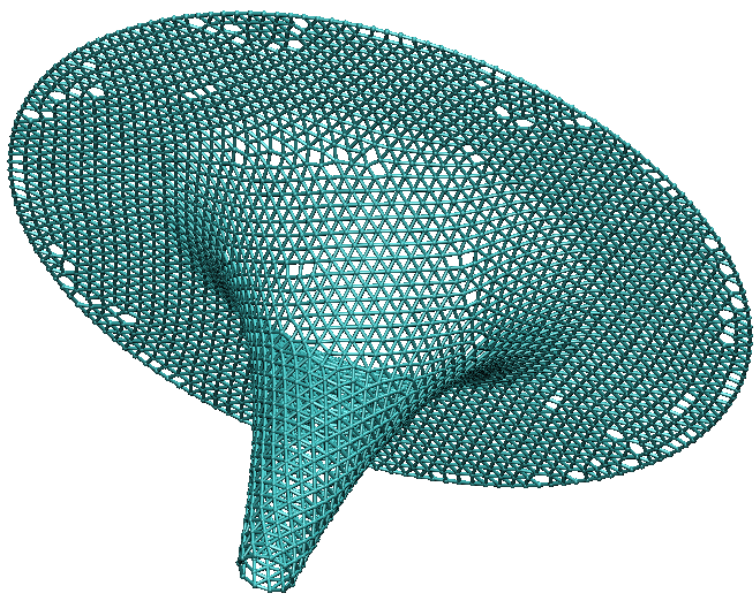
Hard spheres interacting through empirical pair-wise potential (LJ)



Computer simulation can find the equilibrium structure or dynamical properties of many carbon-based materials and work particularly well on rare-gas elements, such as helium and argon, due to their closed shell electronic structure.

We can do better and use 3-body interaction terms (Stillinger-Weber, Tersoff-Brenner, ReaxFF)

$$\Phi(1, \dots, N) = \sum_i v_1(i) + \sum_{i < j} v_2(i, j) + \sum_i v_1(i) + \sum_{i, j, k} v_3(i, j, k) + \dots$$



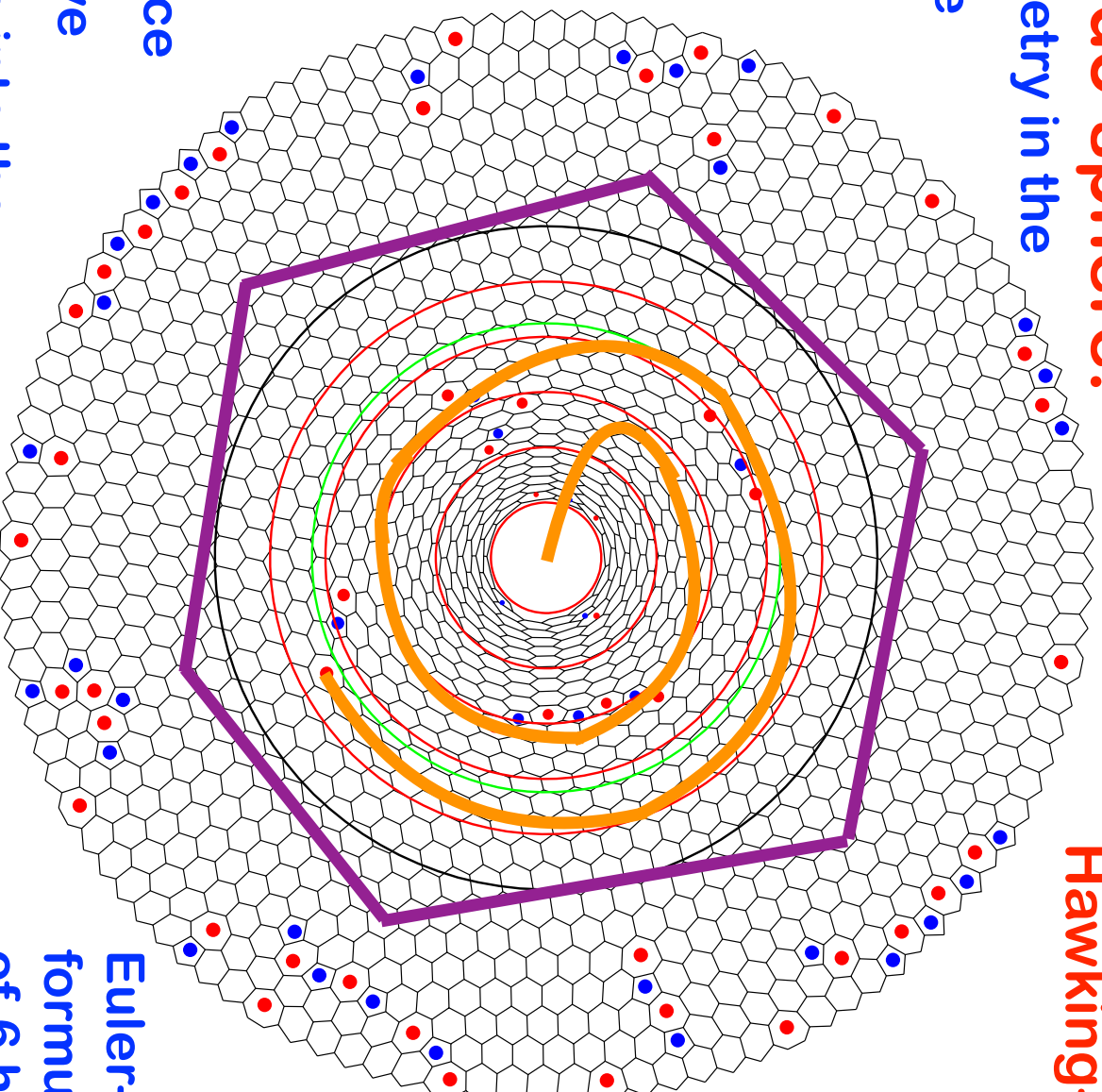
Intermezzo : Graphene trumpets

Beltrami pseudo-sphere:

Lobachevsky geometry in the

Euclidean 3D space

**Find a signature of the
Hawking-Unruh effect**



Embedding a surface

of constant negative

Gaussian curvature into the

real Euclidean 3D-space to mimic a black-hole

Euler-Poincare

formula: an excess

of 6 heptagons with

respect to pentagons

Area = $2.4 \times 3.8 = 9.12$

amorphous glycine-rich
(CHARMM27)

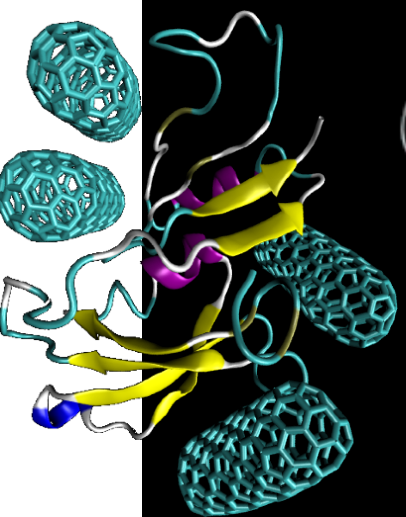
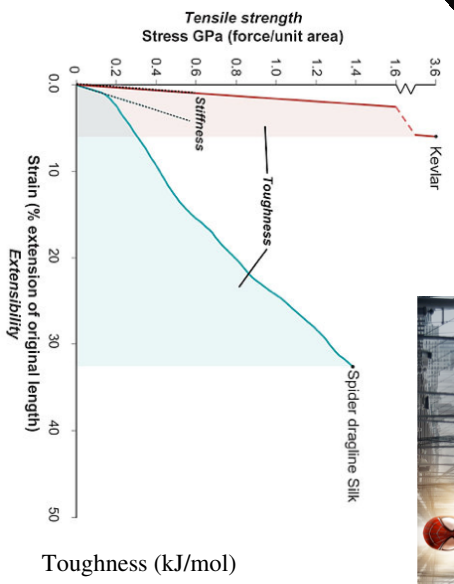
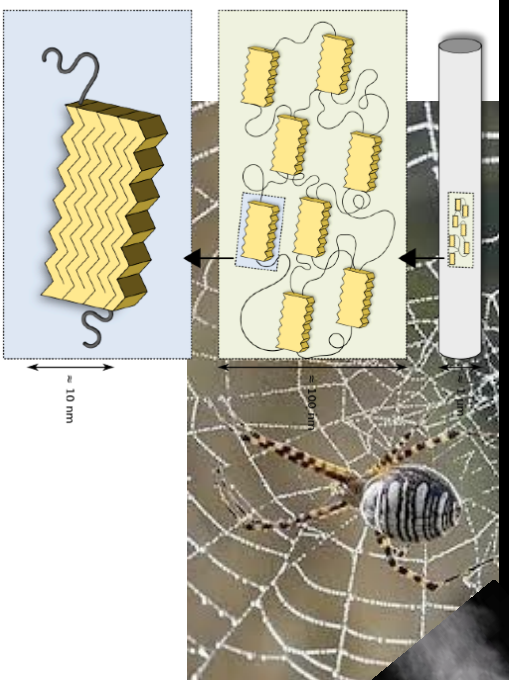
graphene
(DREIDING)

quasi-crystalline poly-
alanine central region
(CHARMM27)

F equally
distributed

15 fibers of amino acids MASP1

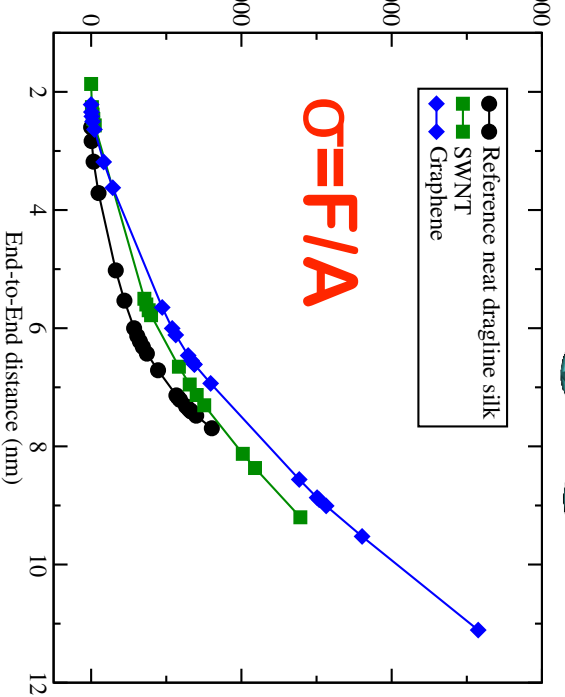
F equally
distributed



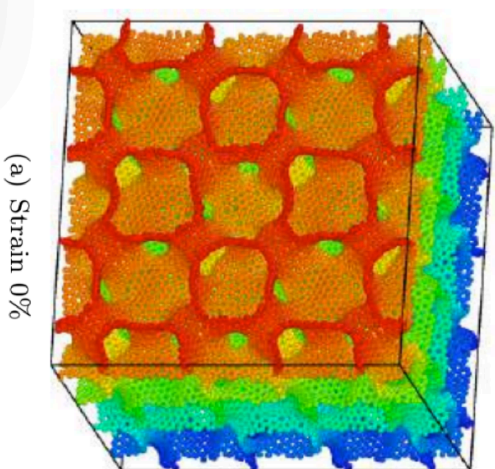
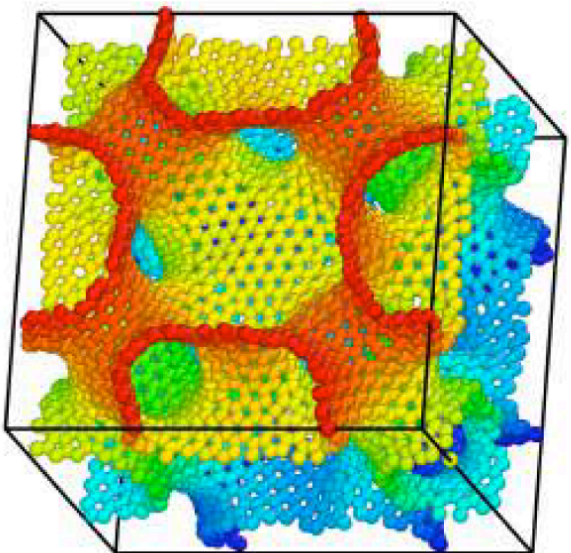
After CG minimization, we perform 150 ps MD runs at $T=10K$, followed by 500 ps at $T=300K$

ϵ =distance between COM of head and tail/original length

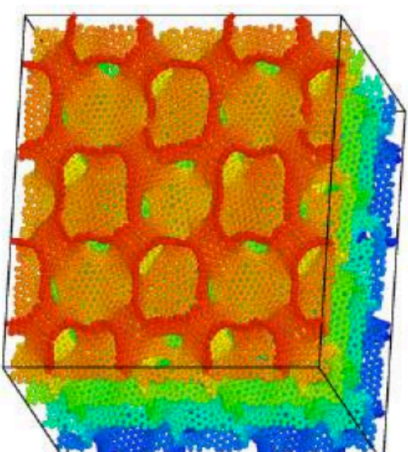
2D MATERIALS 4 (3), 031013/1-9 (2017)



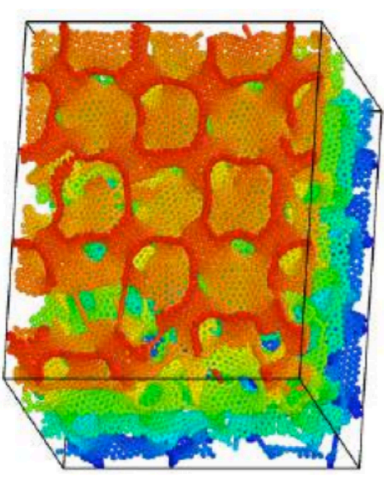
Graphene foams



(a) Strain 0%

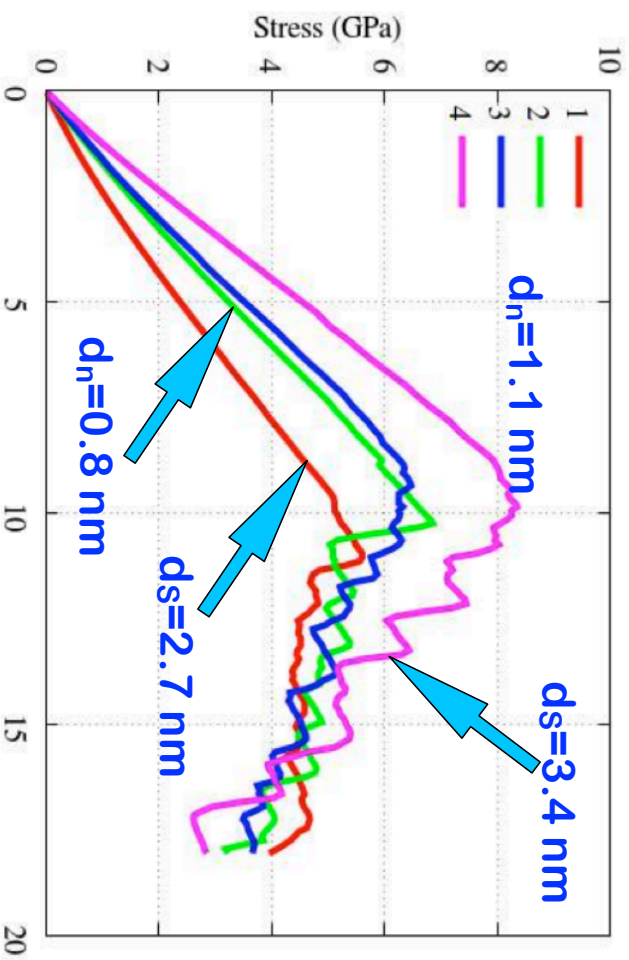


(b) Strain 10%

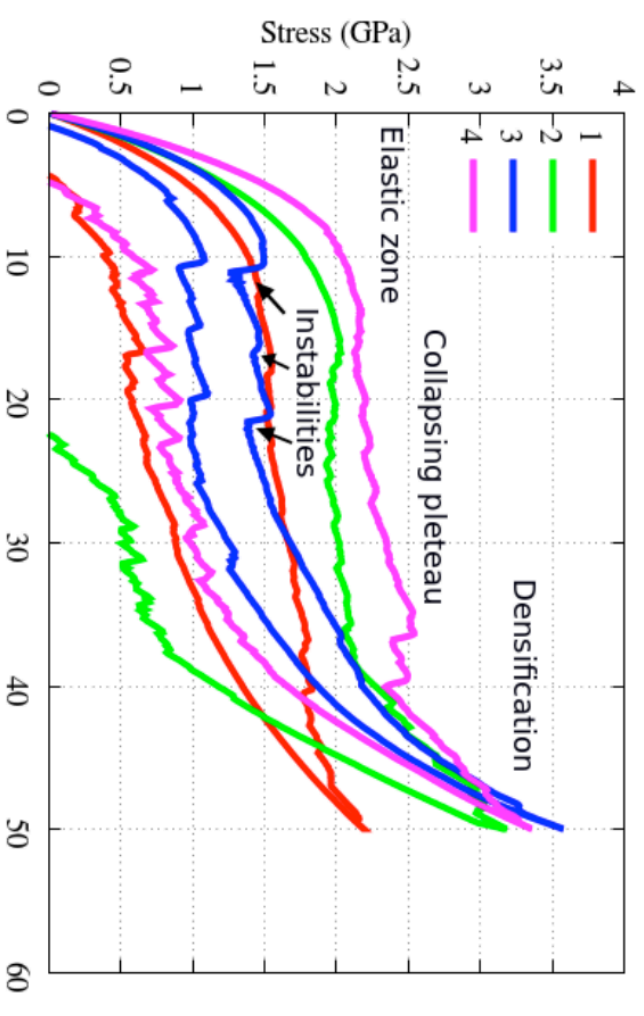


(c) Strain 20%

Tension [100]



Compression [111]



Carbon 111, 796 (2017)

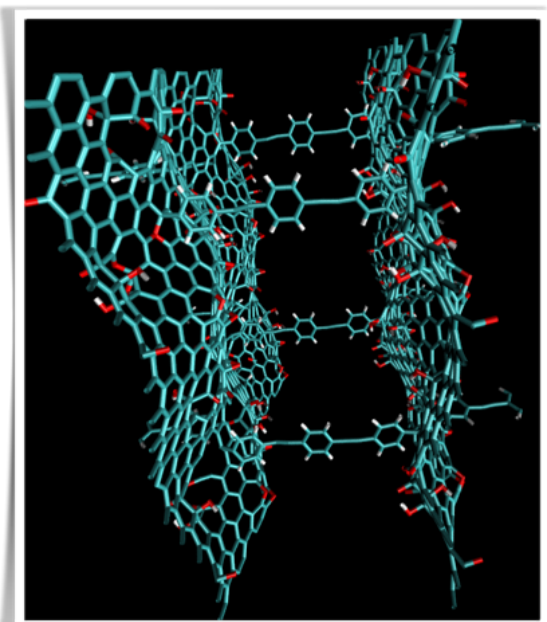
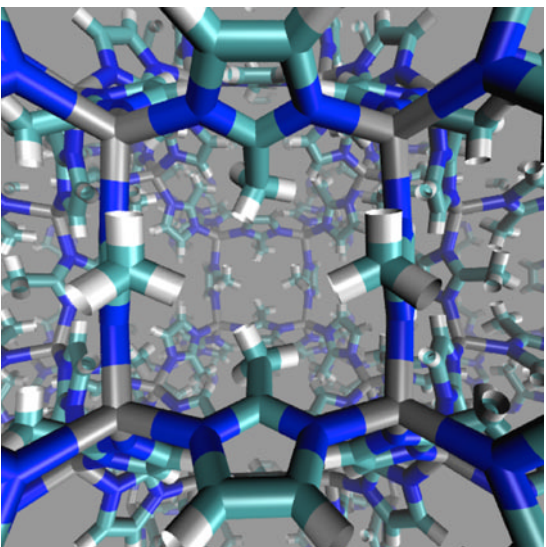
Strain (%)

Strain rate=0.001 ps⁻¹

Strain (%)

Pillared GO

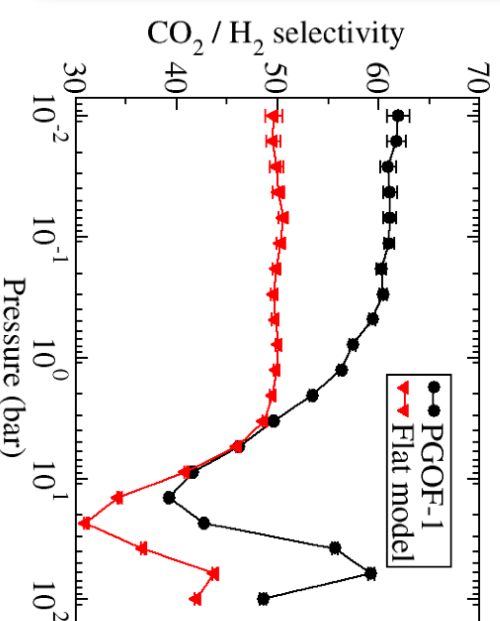
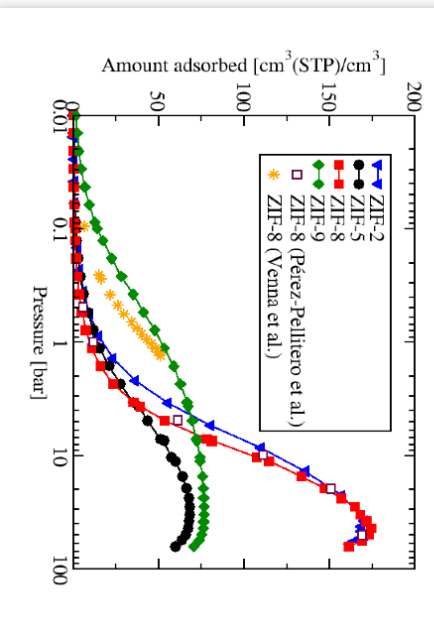
ZIF, MOF and PGO for gas separation and storage

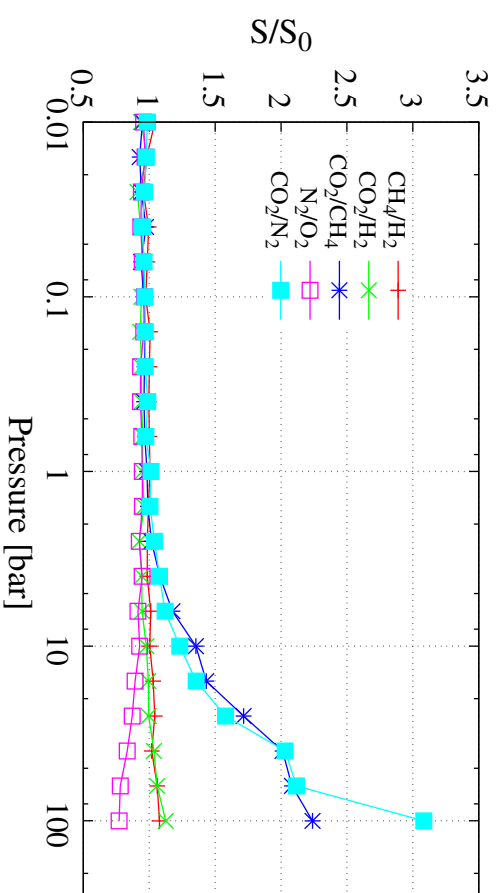
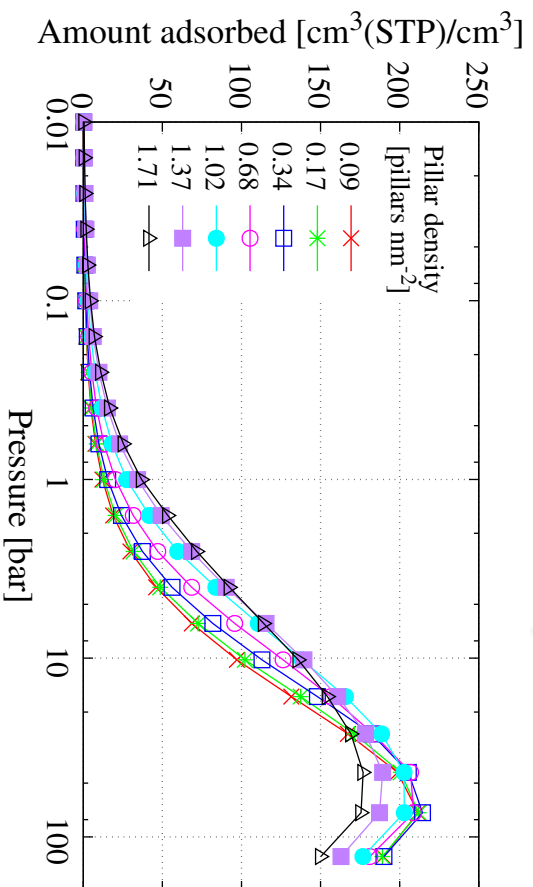
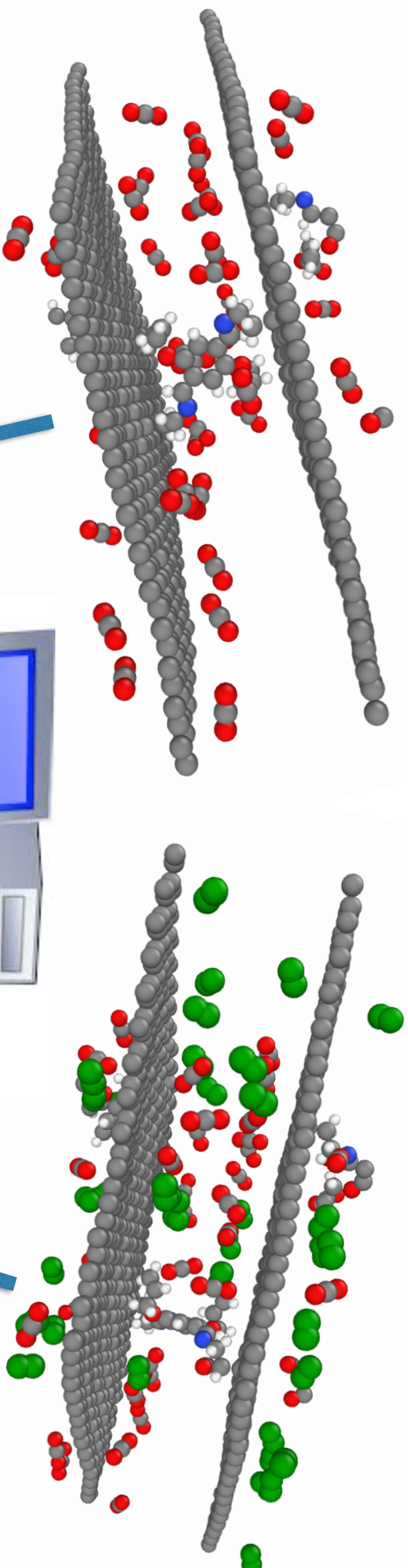


GC Monte Carlo techniques

- ❖ Dispersion (LJ)
- ❖ Interaction (DREIDING or Universal Force Field) + charges (from DFTB simulations)
- ❖ Grand canonical ensemble (fixed temperature, cell volume and chemical potential = external pressure)
- ❖ Usual insertion/deletion + translation/rotation moves
- ❖ Metropolis leads to equilibration

CO₂ in ZIFs @ 298K



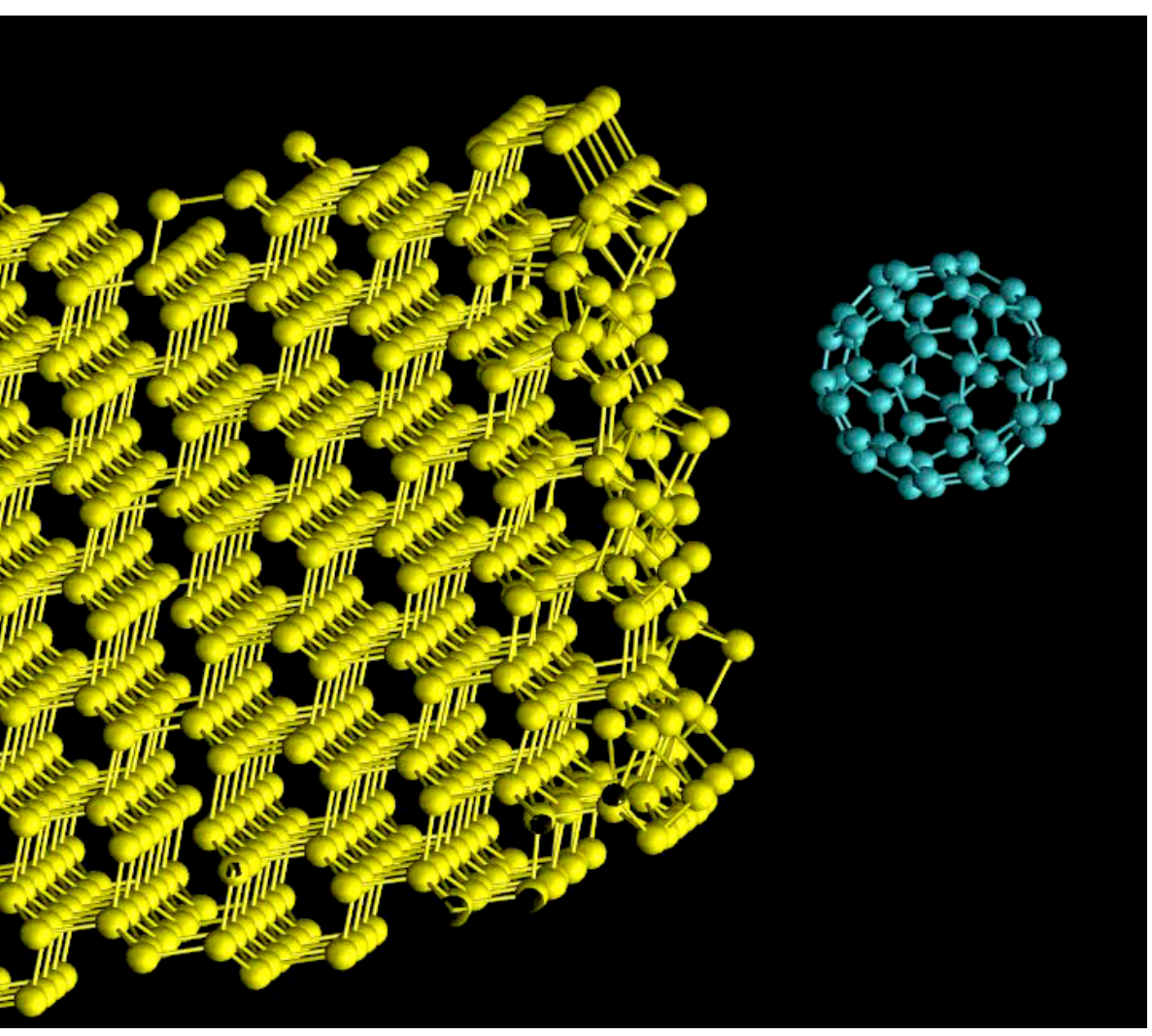


Application of classical RT MD (450 eV)

REGIMES AT ROOM T

1. **< 30 eV: CLUSTER DEPOSITION AND CHEMISORPTION OF THE CLUSTER AS A WHOLE**
2. **30-100 eV: SURFACE PENETRATION**
3. **100-300 eV: PARTIAL FRAGMENTATION**
4. **300-500 eV: SURFACE SPREADING AND CAGE DISRUPTION**
5. **500-1000 eV: CRATER FORMATION**
6. **> 1 KeV: SPUTTERING**

- Computer simulations are in complete disagreement with experiments.
- Si structural order is kept. No evidence of C₆₀ cage breaking, with superficial permeation up to an energy per atom 10 times the experimental one.



C₆₀ impact on Si seems totally out of reach of classical molecular dynamics.

This model has frozen electronic structure and potential is simple pair (no chemistry or description of out-of-equilibrium)

BO-DFT
AT 50 eV

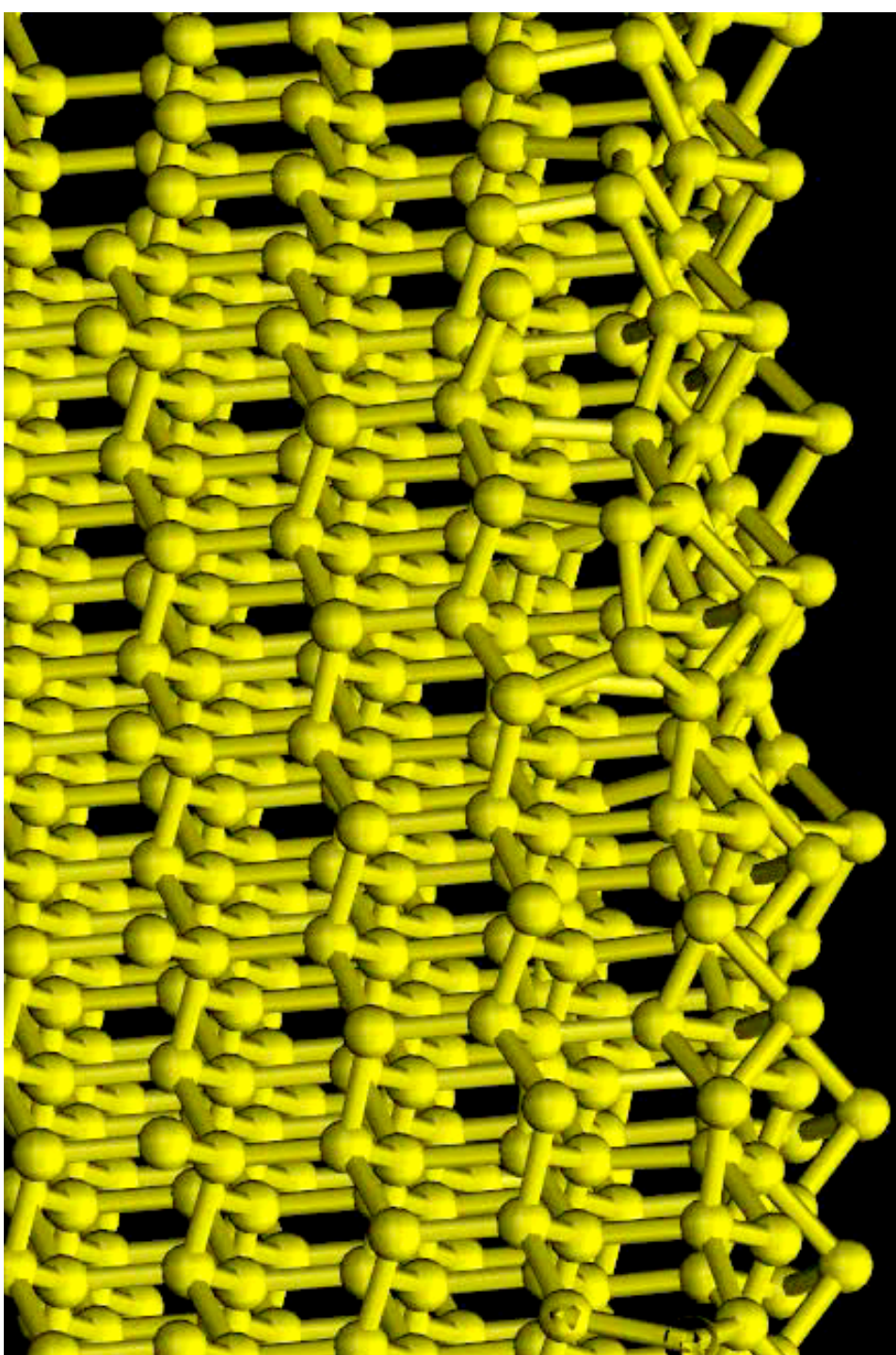
EX-corr:
LDA

PP:
LDA/GGA
PAW 500 eV
cut-off

Sampling:

Γ point

4 seasons Vivaldi



Can DFT be so much in error? What is missing?

Is the BO one-electron state model reliable for SiC?

Ionic vibration period: 10^{12} Hz

Electronic transitions freq.: 10^{17} Hz

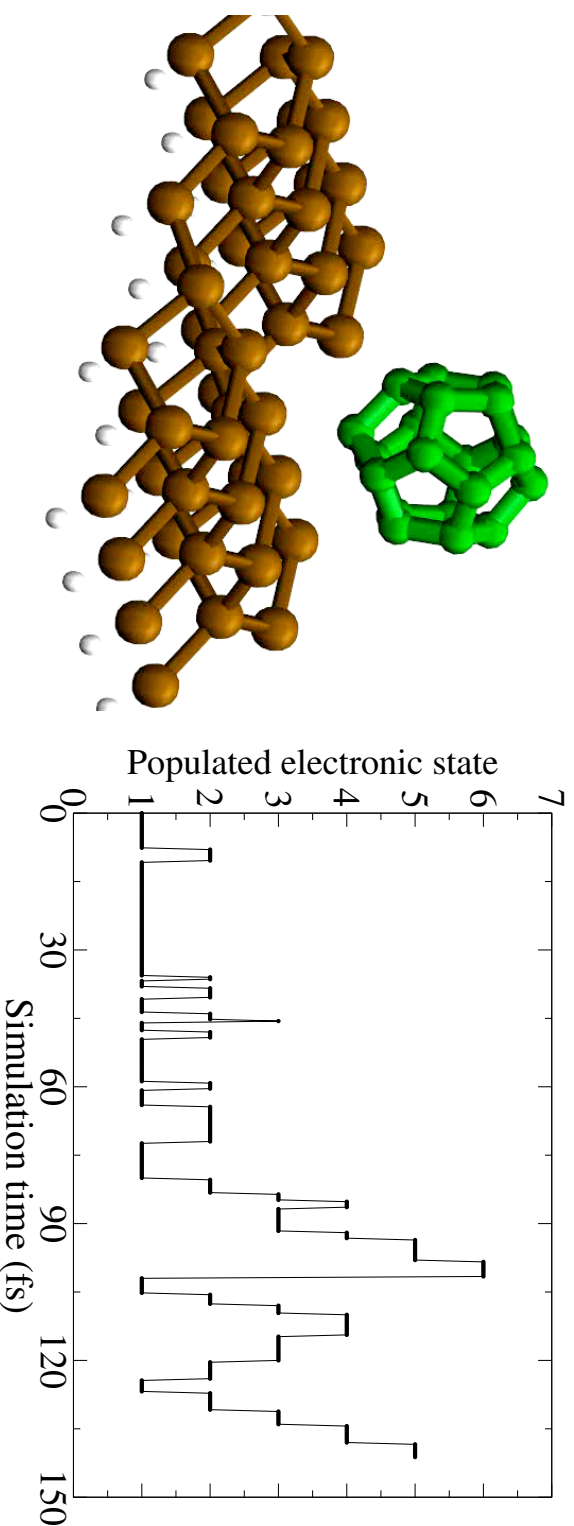
$$\chi = \tau_p / \tau_e = 10^5$$

1.6 eV band-gap corresponds to emission in the region of 10^{15} Hz, collision time scales are of the order of few femto-seconds:

$$\chi \simeq 1$$

Timescales are comparable!!! Electrons cannot relax fast enough to the ground state relative to the instantaneous configuration of the nuclei.

Beethoven: Ode to joy



Forces used in the MD simulation are calculated on the pure adiabatic PES populated at the present MD step.

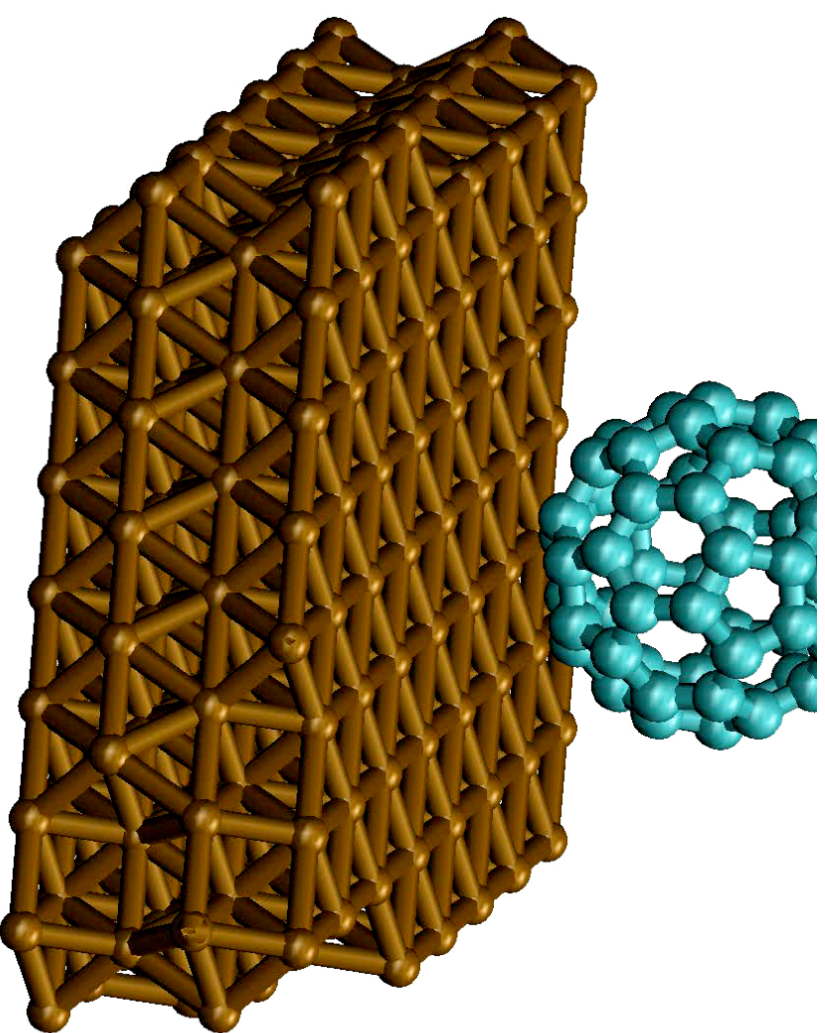
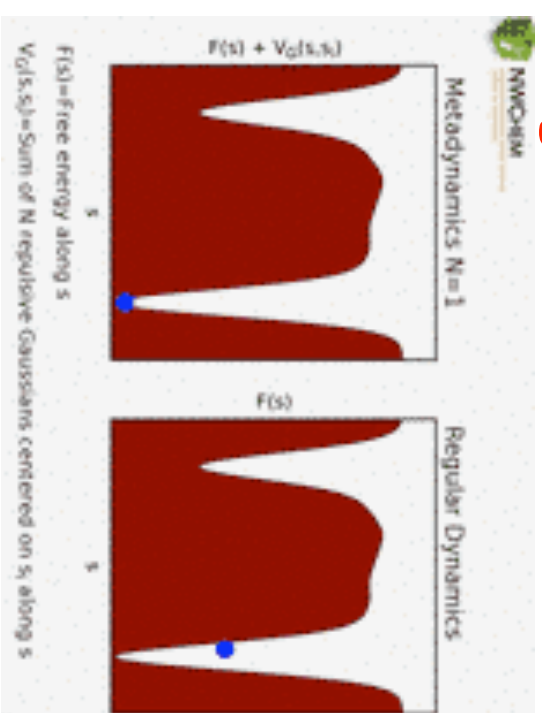
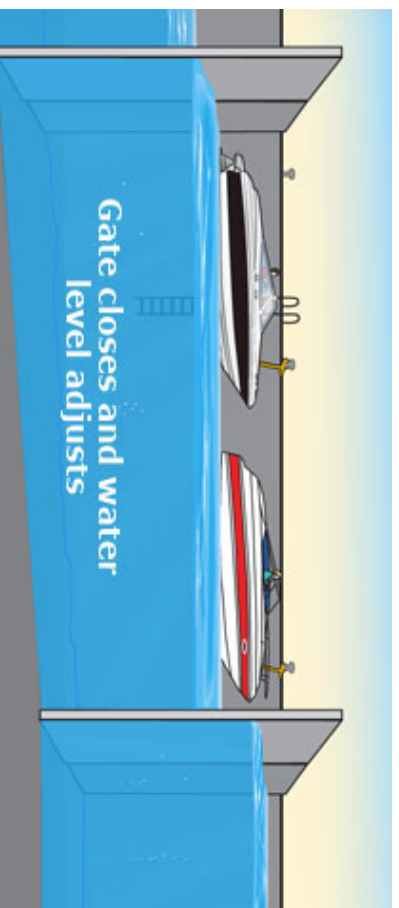
The electrons “lag behind” the nuclei during the collision. PES on which nuclei move changes significantly, possibly allowing for cage breaking at lower kinetic energy.

First multiscale: metadynamics

Large potential barriers (long waiting times) make it difficult to explore configurational space (typically > 1 microsec)

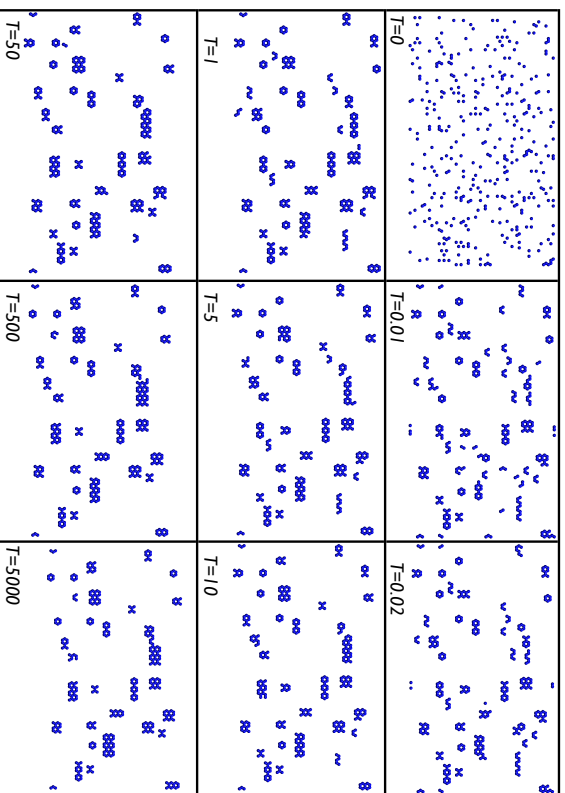
Metadynamics has been developed as a tool to increase sampling efficiency.

Drop repulsive Gaussians in the places already visited until the basins are filled and the system jumps to another place in the configuration space (same trick used for ships with gates)

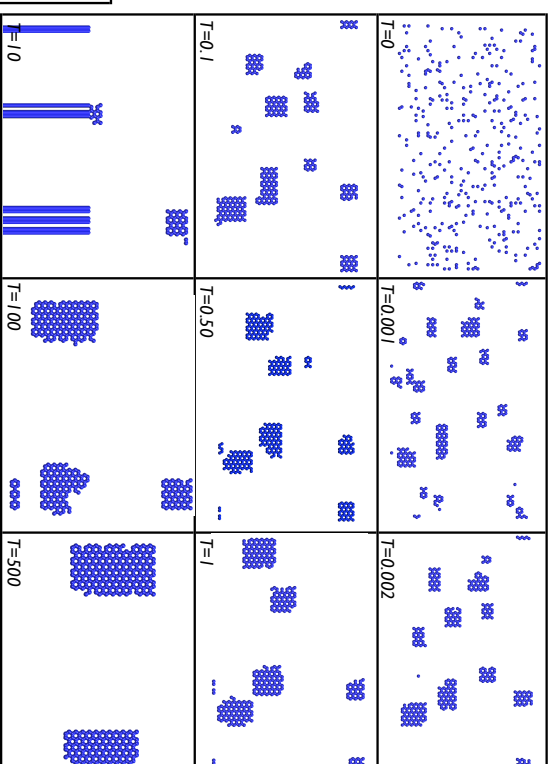


Second multiscale: KMC + NEB

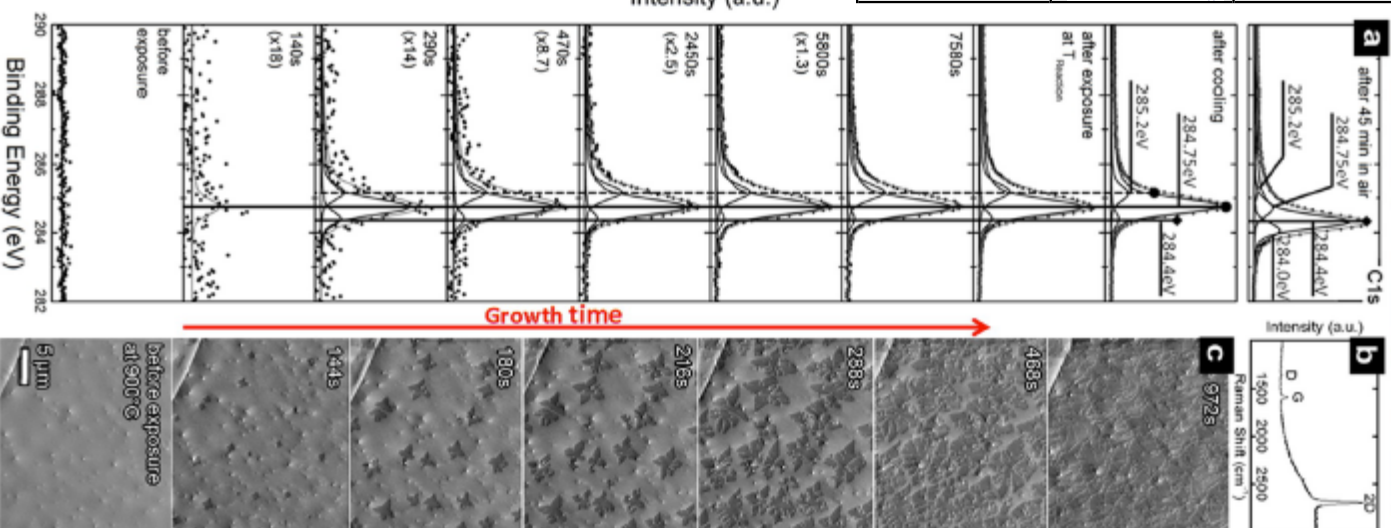
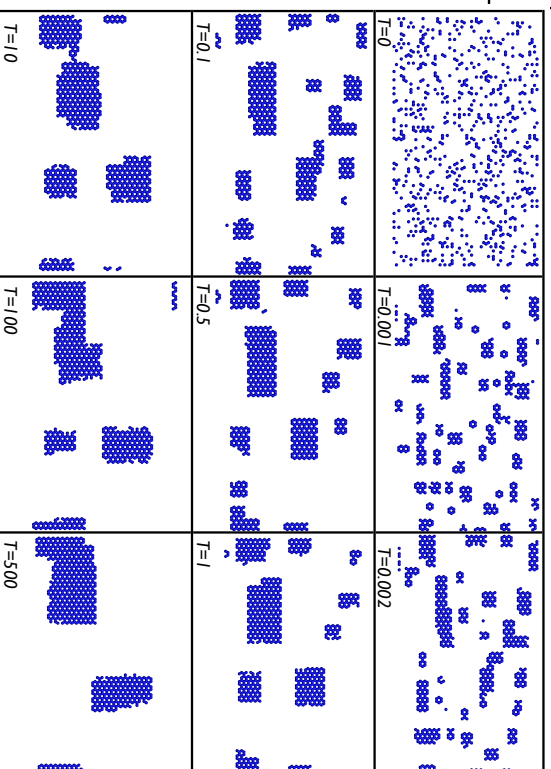
**T = 900 K,
coverage
= 10%**



**T = 900 K,
coverage
= 20%**

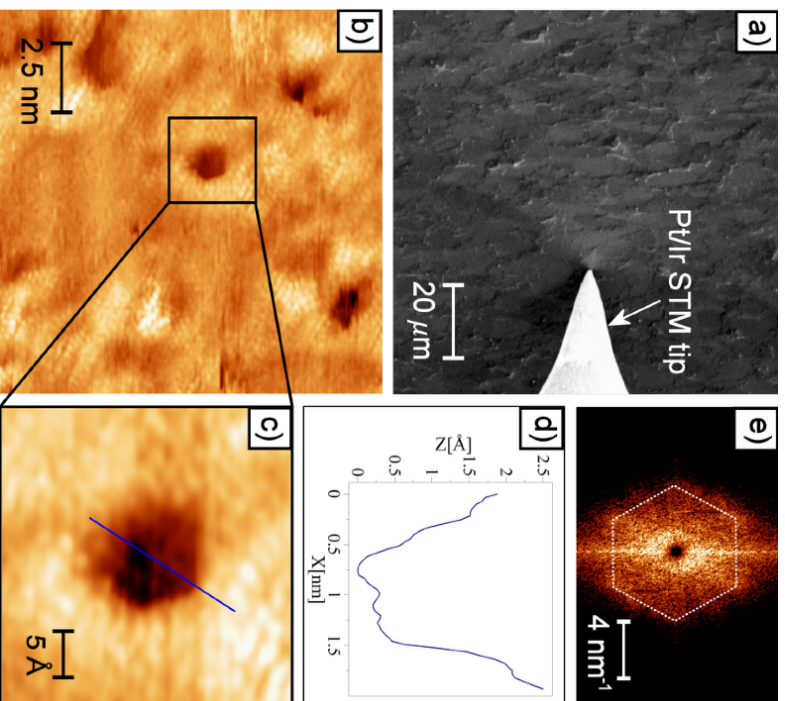


**T = 600 K,
coverage
= 10%**

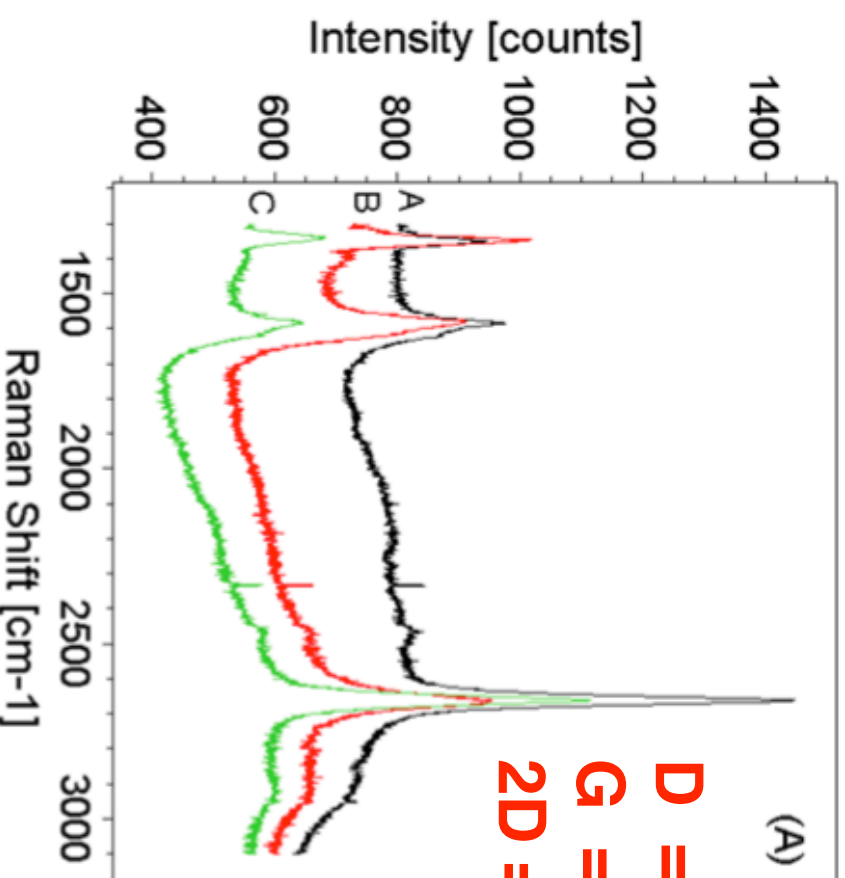


C_{60} deposited by SUMBE, after a surface reconstruction inducing a tighter interaction with Cu, creates favorable conditions for cage unzipping via thermally activated processes at 645 °C (\ll CVD).

C_{60} 1ML on Cu(111) after annealing at 645 °C.



SEM (a) and STM (b-e) analysis. c) details of a dark region, with line profile (d), compatible with fault lines on the top of the metal ; e) FFT analysis of the image in b) showing few nm extended graphene-like domains.

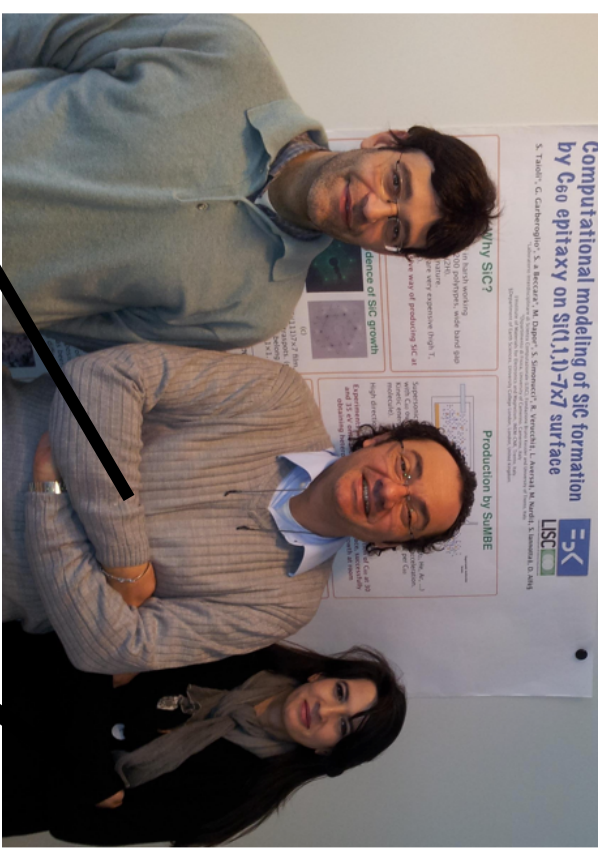


D = 1349 cm⁻¹
G = 1589 cm⁻¹
2D = 2665 cm⁻¹

I(D)/I(G) intensity ratio (0.71, 1.07 and 0.84) assesses the defect density = certain degree of defected G with d-d = 20 nm

I must thank....

S. Simonucci
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Theory

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CNR-FBK

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CNR-FBK



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UGL

